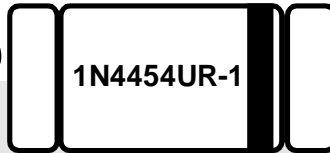


# MINI-MELF-SMD



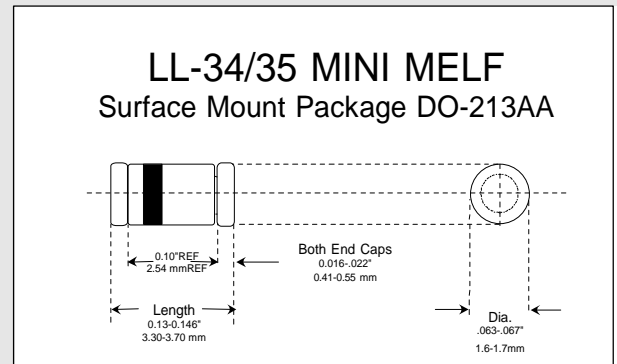
# Silicon Switching Diode

## Applications

Used in general purpose applications, where performance, space and switching speed are important.

## Features

- Six sigma quality
- Metallurgically bonded
- BKC's Sigma Bond™ plating for problem free solderability
- Also comes in DO-35 glass package
- Full UR approval to Mil-S-19500 /144
- Available up to JANTXV levels
- "S" level screening available to Source Control Drawings



Maximum Ratings	Symbol	Value	Unit
Peak Inverse Voltage @ 5 $\mu$ A & 0.1 $\mu$ A @ -55 $^{\circ}$ C	PIV	75 (Min.)	Volts
Average Rectified Current	$I_{Avg}$	200	mAmps
Continuous Forward Current	$I_{Fdc}$	300	mAmps
Peak Surge Current ( $t_{peak} = 1$ sec.)	$I_{peak}$	1.0	Amp
Power Dissipation $T_L = 50$ $^{\circ}$ C, $L = 3/8$ " from body	$P_{tot}$	500	mWatts
Operating Temperature Range	$T_{Op}$	200	$^{\circ}$ C
Storage Temperature Range	$T_{St}$	-65 to +200	$^{\circ}$ C
Electrical Characteristics @ 25 $^{\circ}$ C*	Symbol	Limits	Unit
Forward Voltage @ $I_F = 10$ mA	$V_F$	1.0(max)	Volts
Breakdown Voltage @ $I_R = 10$ mA	PIV	75 (min)	Volts
Reverse Leakage Current @ $V_R = 50$ V	$I_R$	0.1 (max)	$\mu$ A
Reverse Leakage Current @ $V_R = 50$ V, $T = 150$ $^{\circ}$ C	$I_R$	100 (max)	$\mu$ A
Capacitance @ $V_R = 0$ V, $f = 1$ MHz	$C_T$	2.0 (max)	pF
Reverse Recovery Time (note 1)/(note 2)	$t_{rr}$	2.0/4.0 (max)	nSecs
Forward Recovery Voltage (note 3)	$V_{fr}$	3.0 (max)	Volts

Note 1: Per Method 4031-A with  $I_F = I_R = 10$  mA,  $R_L = 100$  Ohms,  $C = 3$  Pf.

Note 2: Per Method 4031-A with  $I_F = 10$  mA,  $R_L = 100$  Ohms,  $V_r = 6$  V, Recover to 1.0 mA.

Note 3: Per Method 4026 with  $I_F = 100$  mA,  $R_L = 50$  Ohms, Peak Square wave, 100 nSec Pulse Width,  $t_r < 30$  nSec, repetition Rate = 5 - 100 KHz. \*Unless Otherwise Specified



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